Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A thin film capacitance element, comprising a lower portion electrode, a dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, and an upper portion electrode are successively formed on the substrate, wherein:

the bismuth layer compound is composed of a thin film capacitance element composition;

the bismuth layer compound is expressed by a composition formula of $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ or $Bi_2A_{m-1}B_mO_{3m+3}$, wherein:

"m" is an even number,

"A" is at least one element selected from Na, K, Pb, Ba, Sr, Ca and Bi, and

"B" is at least one element selected from Fe, Co, Cr, Ga, Ti, Nb, Ta, Sb, V, Mo and W; ~~and~~

Bi in said bismuth layer compound is excessively included with respect to said composition formula of $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ or $Bi_2A_{m-1}B_mO_{3m+3}$, and the excessive content of Bi is in a range of $0 < Bi < 0.5xm$ mol in terms of Bi;

a c-axis orientation degree of the bismuth layer compound is 80% or higher; and

the lower portion electrode is oriented in a [100] direction.

2. (Currently Amended) The thin film capacitance element ~~dielectric thin film~~ as set forth in claim 1, wherein the excessive content of Bi in the dielectric thin film is in a range of $0.4 \leq Bi < 0.5xm$ mol in terms of Bi.

3. (Currently Amended) A thin film capacitance element, comprising a lower portion electrode, a dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, and an upper portion electrode are successively formed on the substrate, wherein:

the bismuth layer compound is composed of a thin film capacitance element composition;

the bismuth layer compound is expressed by a composition formula of $SrBi_4Ti_4O_{15}$; ~~and~~

Bi in the bismuth layer compound is excessively included with respect to said composition formula of $SrBi_4Ti_4O_{15}$, and the excessive content of Bi is in a range of $0 < Bi <$ ~~0.5xm~~ 2.0 mol in terms of Bi;

a c-axis orientation degree of the bismuth layer compound is 80% or higher; and

the lower portion electrode is oriented in a [100] direction.

4. (Currently Amended) A thin film capacitance element, comprising a lower portion electrode, a dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, and an upper portion electrode are successively formed on the substrate, wherein:

the bismuth layer compound is composed of a thin film capacitance element composition;

the bismuth layer compound is expressed by a composition formula of $SrBi_4Ti_4O_{15}$; ~~and~~

Bi in the bismuth layer compound is excessively included with respect to said composition formula of $SrBi_4Ti_4O_{15}$, and when the excessive content of Bi is expressed by a mole ratio (Bi/Ti) against Ti, Bi/Ti is in a range of $1 < Bi/Ti < 1.5$;

a c-axis orientation degree of the bismuth layer compound is 80% or higher; and

the lower portion electrode is oriented in a [100] direction.

5. (Currently Amended) A thin film capacitance element, comprising a lower portion electrode, a dielectric thin film including a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface, and an upper portion electrode are successively formed on the substrate, wherein:

the bismuth layer compound is composed of a thin film capacitance element composition;

the bismuth layer compound is expressed by a composition formula of $Sr_xCa_yBa_zBi_4Ti_4O_{16}$, $x+y+z=1$, $0 \leq x \leq 1$, $0 \leq y \leq$ ~~and $0 \leq z \leq 1$~~, and $0 \leq z \leq 1$; and

Bi in the bismuth layer compound is excessively included with respect to said composition formula of $Sr_xCa_yBa_zBi_4Ti_4O_{15}$, and when the excessive content of Bi is expressed by a mole ratio (Bi/Ti) against Ti, Bi/Ti is in a range of $1 < Bi/Ti < 1.5$;

a c-axis orientation degree of the bismuth layer compound is 80% or higher; and

the lower portion electrode is oriented in a [100] direction.

6. (Currently Amended) The thin film capacitance element ~~dielectric thin film~~ as set forth in claim 1, the thin film capacitance element composition further comprising at least one rare earth element selected from the group consiting of Sc, Y, La, Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb and Lu.

7. (Canceled)

8. (Currently Amended) The thin film capacitance element ~~dielectric thin film~~ as set forth in claim 1, wherein leakage current density at electric field intensity of 50 kV/cm is $1x10^{-7}$ A/cm^2 or lower.

9. (Currently Amended) The thin film capacitance element ~~dielectric thin film~~ as set forth in claim 1, wherein an average change rate of a capacitance against a temperature in a range of -55 to +150°C is ±500 ppm/°C with the reference temperature of 25°C.

10. (Canceled)

11. (Currently Amended) The thin film capacitance element as set forth in ~~claim 10~~ claim 1, wherein a thickness of said dielectric thin film is 1 to 1000 nm.

12. (Currently Amended) A thin film multilayer capacitor, ~~wherein~~ comprising a plurality of ~~the~~ dielectric thin films comprising a bismuth layer compound having a c-axis oriented vertically with respect to a substrate surface ~~as set forth in claim 1~~ and internal electrode thin films ~~are~~ alternately stacked on a substrate, wherein:

the bismuth layer compound is composed of a thin film capacitance element composition;

the bismuth layer compound is expressed by a composition formula of $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ or $Bi_2A_{m-1}B_mO_{3m+3}$, wherein:

"m" is an even number,

"A" is at least one element selected from Na, K, Pb, Ba, Sr, Ca, and Bi, and

"B" is at least one element selected from Fe, Co, Cr, Ga, Ti, Nb, Ta, Sb, V, Mo and W;

Bi in said bismuth layer compound is excessively included with respect to said composition formula of $(Bi_2O_2)^{2+}(A_{m-1}B_mO_{3m+1})^{2-}$ or $Bi_2A_{m-1}B_mO_{3m+3}$, and the excessive content of Bi is in a range of $0 < Bi < 0.5xm$ mol in terms of Bi;

a c-axis orientation degree of the bismuth layer compound is 80% or higher; and

the internal electrode thin films are oriented in a [100] direction.

13. (Original) The thin film multilayer capacitor as set forth in claim 12, wherein a thickness of said dielectric thin film is 1 to 1000 nm.

14-24. (Canceled)

25. (New) The thin film capacitance element as set forth in claim 1, wherein the lower portion electrode comprises a conductive oxide or precious metal.

26. (New) The thin film capacitance element as set forth in claim 1, wherein the lower portion electrode comprises $CaRuO_3$, $SrRuO_3$, Pt, or Ru.